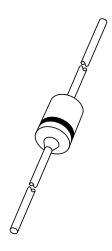
# DISCRETE SEMICONDUCTORS

# DATA SHEET



# **BYD11 series**Controlled avalanche rectifiers

Product specification
Supersedes data of April 1996
File under Discrete Semiconductors, SC01

1996 Sep 26



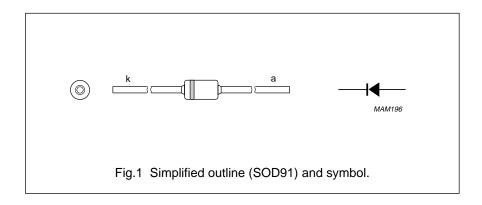


# Controlled avalanche rectifiers

## **BYD11 series**

#### **FEATURES**

- · Glass passivated
- High maximum operating temperature
- Low leakage current
- · Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack.



#### **DESCRIPTION**

Cavity free cylindrical glass package through Implotec<sup>™(1)</sup> technology.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

(1) Implotec is a trademark of Philips.

#### **MARKING**

| TYPE NUMBER | MARKING CODE |
|-------------|--------------|
| BYD11D      | 11D          |
| BYD11G      | 11G          |
| BYD11J      | 11J          |
| BYD11K      | 11K          |
| BYD11M      | 11M          |

# LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL           | PARAMETER                       | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|---------------------------------|------------|------|------|------|
| V <sub>RRM</sub> | repetitive peak reverse voltage |            |      |      |      |
|                  | BYD11D                          |            | _    | 200  | V    |
|                  | BYD11G                          |            | _    | 400  | V    |
|                  | BYD11J                          |            | _    | 600  | V    |
|                  | BYD11K                          |            | _    | 800  | V    |
|                  | BYD11M                          |            | _    | 1000 | V    |
| V <sub>RWM</sub> | crest working reverse voltage   |            |      |      |      |
|                  | BYD11D                          |            | _    | 200  | V    |
|                  | BYD11G                          |            | _    | 400  | V    |
|                  | BYD11J                          |            | _    | 600  | V    |
|                  | BYD11K                          |            | _    | 800  | V    |
|                  | BYD11M                          |            | _    | 1000 | V    |
| $V_R$            | continuous reverse voltage      |            |      |      |      |
|                  | BYD11D                          |            | _    | 200  | V    |
|                  | BYD11G                          |            | _    | 400  | V    |
|                  | BYD11J                          |            | _    | 600  | V    |
|                  | BYD11K                          |            | _    | 800  | V    |
|                  | BYD11M                          |            | _    | 1000 | V    |

FOR REPLACEMENT TYPE SEE INDEX SECTION OF HANDBOOK SC01

# Controlled avalanche rectifiers

BYD11 series

| SYMBOL             | PARAMETER                                     | CONDITIONS  | MIN. | MAX. | UNIT |
|--------------------|---|---|------|------|------|
| I <sub>F(AV)</sub> | average forward current                       | T <sub>tp</sub> = 55 °C;<br>lead length = 10 mm;<br>averaged over any 20 ms<br>period; see Figs 2 and 4                 | 1    | 0.50 | A    |
|                    |   | T <sub>amb</sub> = 60 °C; PCB mounting<br>(see Fig.9);<br>averaged over any 20 ms<br>period; see Figs 3 and 4           | -    | 0.37 | A    |
| I <sub>FSM</sub>   | non-repetitive peak forward current           | t = 10 ms half sinewave;<br>T <sub>j</sub> = T <sub>j max</sub> prior to surge;<br>V <sub>R</sub> = V <sub>RRMmax</sub> | -    | 10   | А    |
| P <sub>RSM</sub>   | non-repetitive peak reverse power dissipation | t = 20 μs half sinewave;<br>$T_j = T_{j \text{ max}}$ prior to surge  | _    | 200  | W    |
| T <sub>stg</sub>   | storage temperature                           |   | -65  | +175 | °C   |
| Tj                 | junction temperature                          | see Fig.5   | -65  | +175 | °C   |

#### **ELECTRICAL CHARACTERISTICS**

 $T_i = 25$  °C; unless otherwise specified.

| SYMBOL             | PARAMETER                           | CONDITIONS  | MIN. | TYP. | MAX. | UNIT |
|--------------------|-------------------------------------|---|------|------|------|------|
| V <sub>F</sub> tzt | forward voltage                     | $I_F = 0.5 \text{ A}; T_j = T_{j \text{ max}}; \text{ see Fig.6}$                       | _    | _    | 0.91 | V    |
|                    |                                     | I <sub>F</sub> = 0.5 A; see Fig.6   | _    | _    | 1.06 | V    |
| V <sub>(BR)R</sub> | reverse avalanche breakdown voltage | I <sub>R</sub> = 0.1 mA   |      |      |      |      |
|                    | BYD11D                              |   | 225  | _    | _    | V    |
|                    | BYD11G                              |   | 450  | _    | _    | V    |
|                    | BYD11J                              |   | 650  | _    | _    | V    |
|                    | BYD11K                              |   | 900  | _    | _    | V    |
|                    | BYD11M                              |   | 1100 | _    | _    | V    |
| I <sub>R</sub>     | reverse current                     | V <sub>R</sub> = V <sub>RRMmax</sub> ; see Fig.7  | _    | _    | 1    | μΑ   |
|                    |                                     | $V_R = V_{RRMmax}$ ; $T_j = 165$ °C; see Fig.7  | _    | _    | 75   | μΑ   |
| t <sub>rr</sub>    | reverse recovery time               | when switched from $I_F$ = 0.5 A to $I_R$ = 1 A; measured at $I_R$ = 0.25 A; see Fig.10 | _    | 3    | _    | μs   |
| C <sub>d</sub>     | diode capacitance                   | V <sub>R</sub> = 0 V; f = 1 MHz; see Fig.8  | _    | 14   | _    | pF   |

#### THERMAL CHARACTERISTICS

| SYMBOL               | PARAMETER                                     | CONDITIONS          | VALUE | UNIT |
|----------------------|---|---------------------|-------|------|
| R <sub>th j-tp</sub> | thermal resistance from junction to tie-point | lead length = 10 mm | 180   | K/W  |
| R <sub>th j-a</sub>  | thermal resistance from junction to ambient   | note 1              | 250   | K/W  |

### Note

1. Device mounted on epoxy-glass printed-circuit board, 1.5 mm thick; thickness of copper  $\geq$ 40  $\mu$ m, see Fig.9. For more information please refer to the "General Part of Handbook SC01".

# Controlled avalanche rectifiers

# BYD11 series

#### **GRAPHICAL DATA**

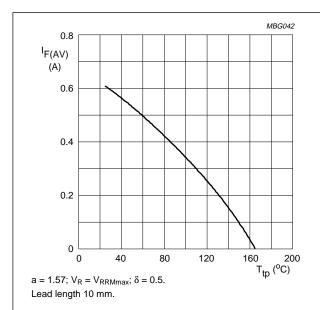


Fig.2 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).

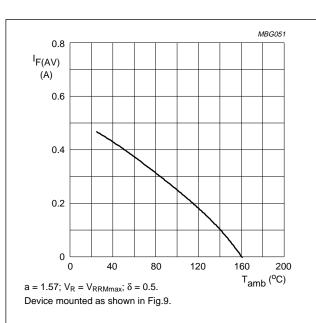
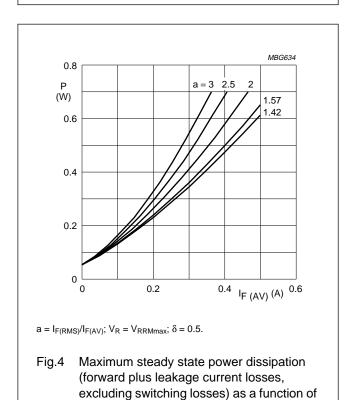
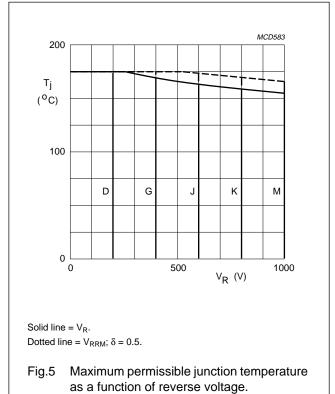


Fig.3 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).

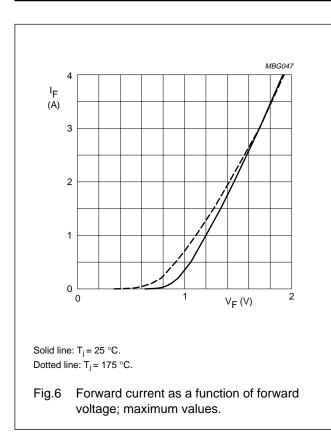


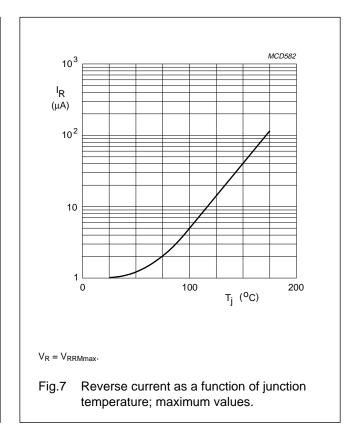
average forward current.

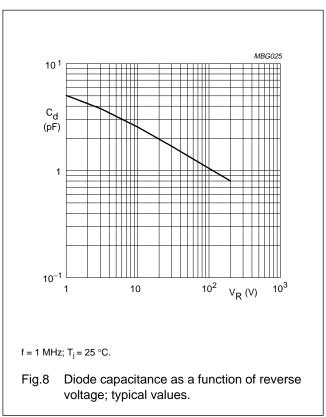


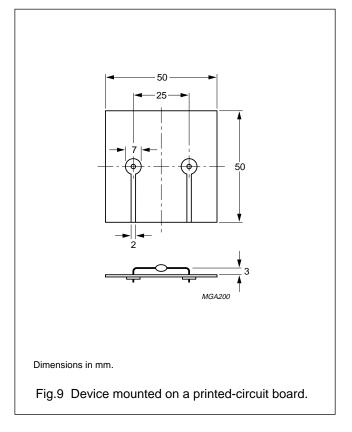
# Controlled avalanche rectifiers

# BYD11 series



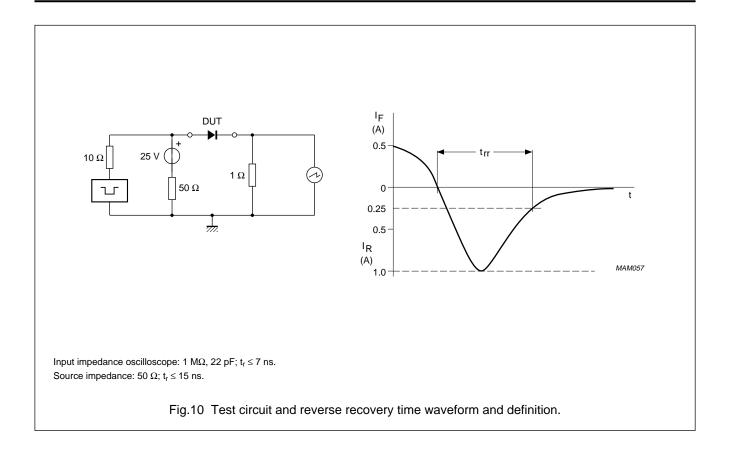






# Controlled avalanche rectifiers

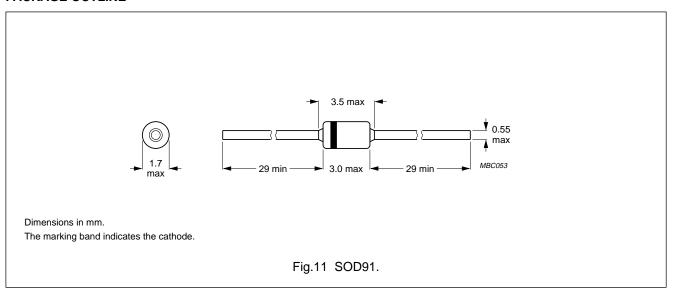
# BYD11 series



# Controlled avalanche rectifiers

**BYD11** series

#### **PACKAGE OUTLINE**



#### **DEFINITIONS**

| Data sheet status         |   |
|---------------------------|---|
| Objective specification   | This data sheet contains target or goal specifications for product development.       |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification     | This data sheet contains final product specifications.                                |
| ,                         |   |

#### **Limiting values**

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

#### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.